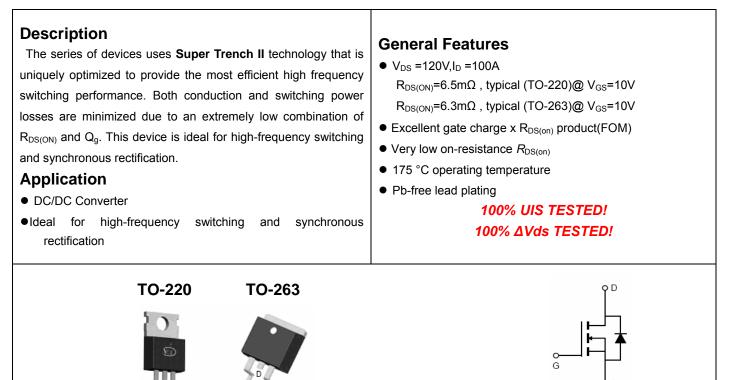


NCE N-Channel Super Trench II Power MOSFET



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP070N12	NCEP070N12	TO-220	-	-	-
NCEP070N12D	NCEP070N12D	TO-263	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	120	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	100	А
Drain Current-Continuous(T _C =100℃)	I _D (100℃)	72	A
Pulsed Drain Current	I _{DM}	400	A
Maximum Power Dissipation	PD	150	W
Derating factor		1.0	W/°C
Single pulse avalanche energy (Note 4)	E _{AS}	450	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case	R _{θJC}	1.0	°C /W	
--------------------------------------	------------------	-----	--------------	--



Electrical Characteristics (T_c=25[°]C unless otherwise noted) Symbol Condition Min Parameter Typ Max Unit **Off Characteristics** Drain-Source Breakdown Voltage V_{GS}=0V I_D=250µA V **BV**_{DSS} 120 _ Zero Gate Voltage Drain Current V_{DS}=120V, V_{GS}=0V IDSS -1 μA Gate-Body Leakage Current IGSS V_{GS}=±20V,V_{DS}=0V ±100 nA _ _ On Characteristics (Note 3) Gate Threshold Voltage V_{DS}=V_{GS}, I_D=250µA 2.0 3.0 4.0 V V_{GS(th)} TO-220 6.5 7.0 Drain-Source On-State Resistance V_{GS}=10V, I_D=50A R_{DS(ON)} mΩ TO-263 6.3 7.0 Forward Transconductance V_{DS}=5V,I_D=50A 60 _ S **g**_{FS} Dynamic Characteristics (Note3) Input Capacitance Clss 3450 pF _ _ V_{DS}=60V, V_{GS}=0V, **Output Capacitance** C_{oss} 390 pF _ _ F=1.0MHz **Reverse Transfer Capacitance** C_{rss} 18 рF _ _ Switching Characteristics (Note 3) Turn-on Delay Time 20 nS t_{d(on)} _ Turn-on Rise Time tr 15 nS _ _ V_{DD} =60V,I_D=50A V_{GS}=10V,R_G=1.6Ω Turn-Off Delay Time 40 t_{d(off)} -_ nS Turn-Off Fall Time tf -10 nS **Total Gate Charge** 57 nC Qq -_ V_{DS}=60V,I_D=50A, Gate-Source Charge 21 Q_{qs} nC --V_{GS}=10V Gate-Drain Charge Q_{gd} 13 nC **Drain-Source Diode Characteristics** Diode Forward Voltage (Note 2) V_{SD} V_{GS}=0V,I_S=50A 1.2 V _ _ **Diode Forward Current** 100 А $I_{\rm S}$ _ _ $T_J = 25^{\circ}C, I_F = 100A$ nS **Reverse Recovery Time** t_{rr} -70 $di/dt = 100A/\mu s^{(Note3)}$ 110 **Reverse Recovery Charge** Qrr -nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

3. Guaranteed by design, not subject to production

4. EAS condition : Tj=25 $^\circ C$,V_DD=50V,V_G=10V,L=0.25mH,Rg=25 Ω



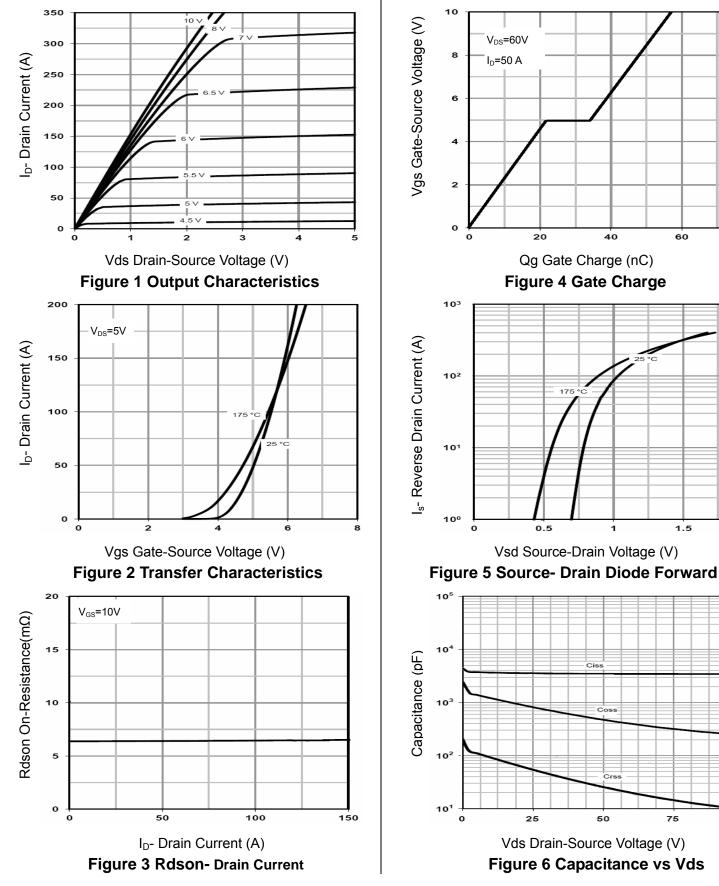
40

60

1.5

80

Typical Electrical and Thermal Characteristics



100

75



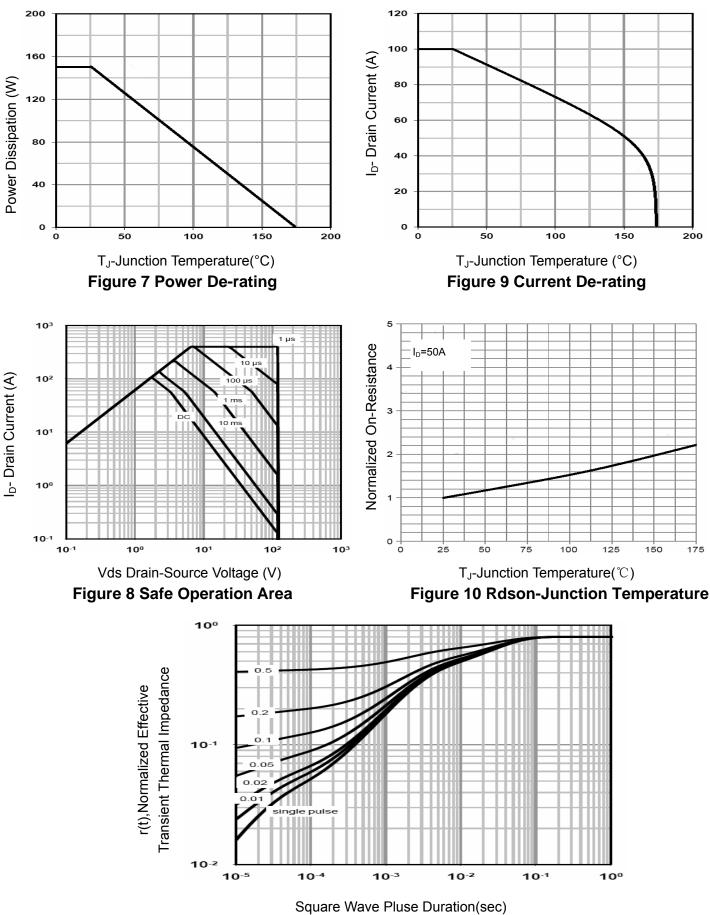
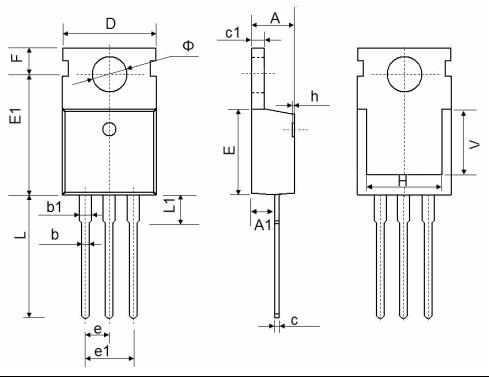


Figure 11 Normalized Maximum Transient Thermal Impedance



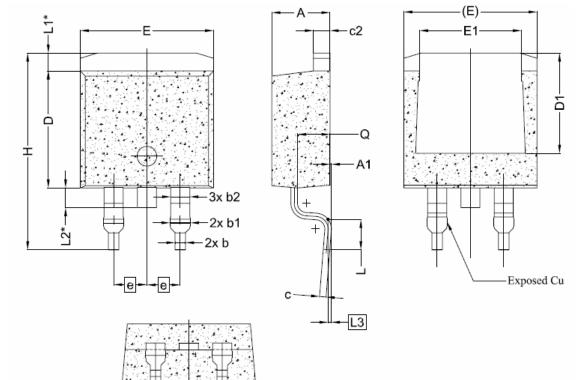
TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
А	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
С	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
е	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
Н	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276	REF.
Ф	3.400	3.800	0.134	0.150



TO-263-2L Package Information



Ourseland	Dimensions In Millimeters			
Symbol	Min.	Nom.	Max.	
A	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
с	0.40	0.50	0.60	
c2	1.15	1.27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	-	
E	9.96	10.16	10.36	
E1	6.89	7.77	7.89	
е	2.54BSC			
Н	14.61	15.00	15.88	
L	1.78	2.32	2.79	
L1	1.36 REF.			
L2	1.50 REF.			
L3	0.25 BSC			
Q	2.30	2.48	2.70	



Attention:

- Any and all NCE power products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your NCE power representative nearest you before using any NCE power products described or contained herein in such applications.
- NCE power assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all NCE power products described or contained herein.
- Specifications of any and all NCE power products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- NCE power Semiconductor CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all NCE power products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of NCE power Semiconductor CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. NCE power believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the NCE power product that you intend to use.
- This catalog provides information as of Sep.2010. Specifications and information herein are subject to change without notice.